

**Amendments to the Claims**

1. *(Previously Presented)* An electric device with a body having a resistor comprising a phase change material being changeable between a first phase and a second phase, the resistor having an electric resistance which depends on whether the phase change material is in the first phase or the second phase, the resistor being able to conduct a current for enabling a transition from the first phase to the second phase, the phase change material being a fast growth material.
2. *(Previously Presented)* An electric device as claimed in Claim 1, wherein the phase change material has a crystallization speed of at least 1 m/s.
3. *(Previously Presented)* An electric device as claimed in Claim 1, wherein the phase change material is a composition of formula  $Sb_{1-c}M_c$ , with c satisfying  $0.05 \leq c \leq 0.61$ , and M being one or more elements selected from the group of Ge, In, Ag, Ga, Te, Zn and Sn.
4. *(Previously Presented)* An electric device as claimed in Claim 3, wherein c satisfies  $0.05 \leq c \leq 0.5$ .
5. *(Previously Presented)* An electric device as claimed in Claim 4, wherein c satisfies  $0.10 \leq c \leq 0.5$ .
6. *(Previously Presented)* An electric device as claimed in Claim 1, wherein the phase change material is substantially free of Te.
7. *(Previously Presented)* An electric device as claimed in Claim 3, wherein the phase change material comprises Ge or Ga in concentrations which range in total between 5 and 35 atomic percent.

8. *(Previously Presented)* An electric device as claimed in Claim 3, wherein the phase change material comprises In or Sn in concentrations which range in total between 5 and 30 atomic percent.

9. *(Previously Presented)* An electric device as claimed in Claim 1, wherein the phase change material is a composition of formula  $Sb_aTe_bX_{100-(a+b)}$ , with a, b and  $100-(a+b)$  denoting atomic percentages satisfying  $1 \leq a/b \leq 8$  and  $4 \leq 100-(a+b) \leq 22$ , and X being one or more elements selected from the group of Ge, In, Ag, Ga, Zn and Sn.

10. *(Previously Presented)* An electric device as claimed in Claim 9, wherein the phase-change material comprises at least 10 % and less than 22 % Ge.

11. *(Previously Presented)* An electric device as claimed in Claim 9, wherein the resistor has a first contact area and a second contact area, the first contact area being smaller than or equal to the second contact area, the first contact area having a characteristic dimension d (in nm), d being larger than  $6 \cdot a/b$ .

Claims 12-16 *(Cancelled)*